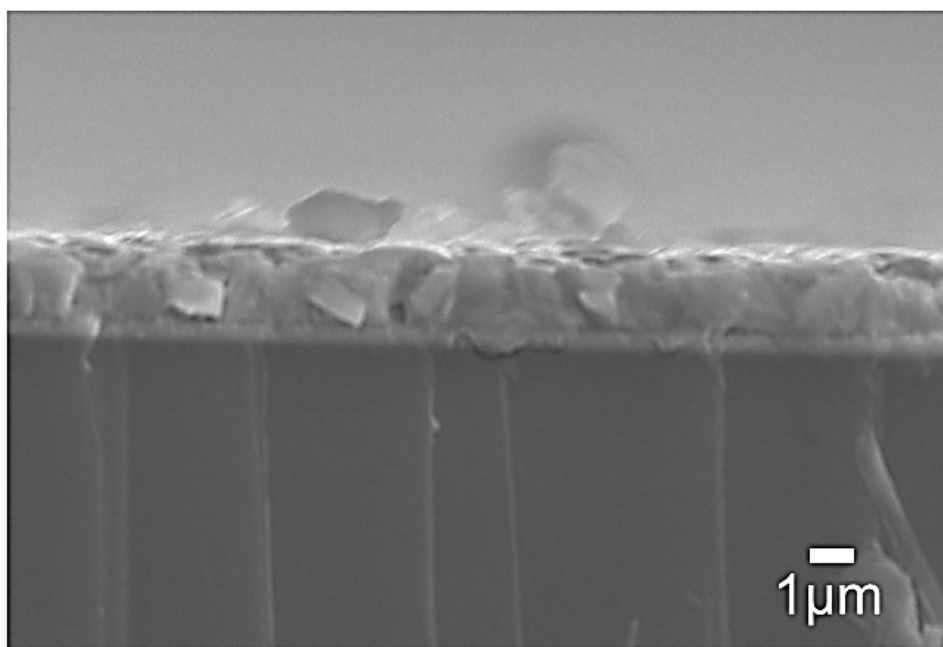


## Impedance spectroscopy of $\text{Sb}_2\text{Se}_3$ photovoltaics consisting of $(\text{Sb}_4\text{Se}_6)_n$ nanoribbons under light illumination

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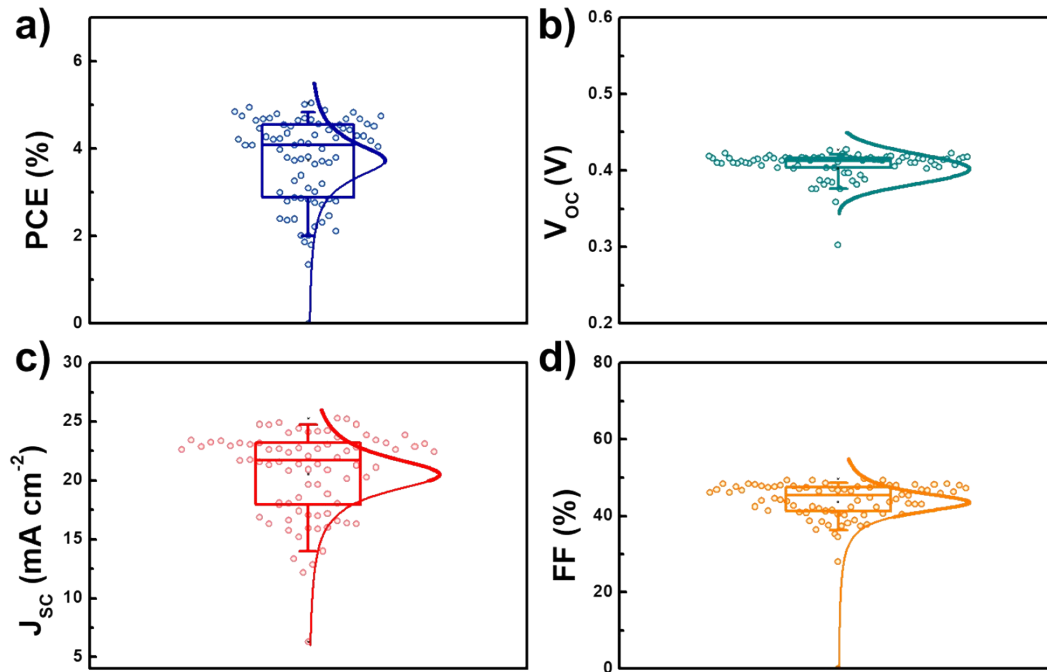
*Tilley, Wooseok Yang\**



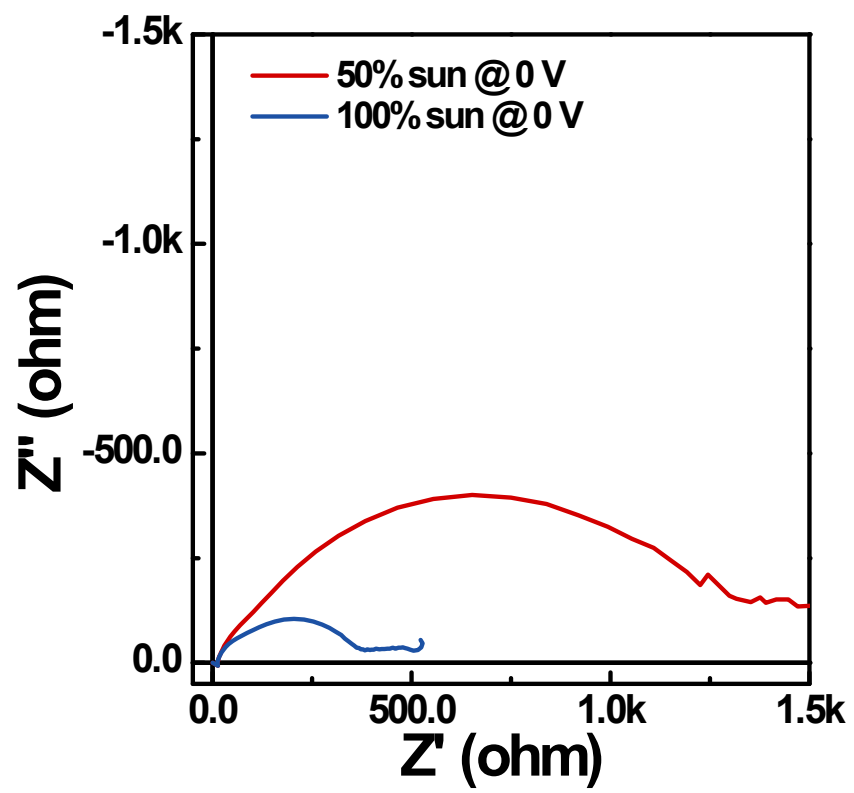
**Figure S1.** Cross-section SEM image of the w-seed  $\text{Sb}_2\text{Se}_3$  film on  $\text{TiO}_2/\text{FTO}$  superstrate.



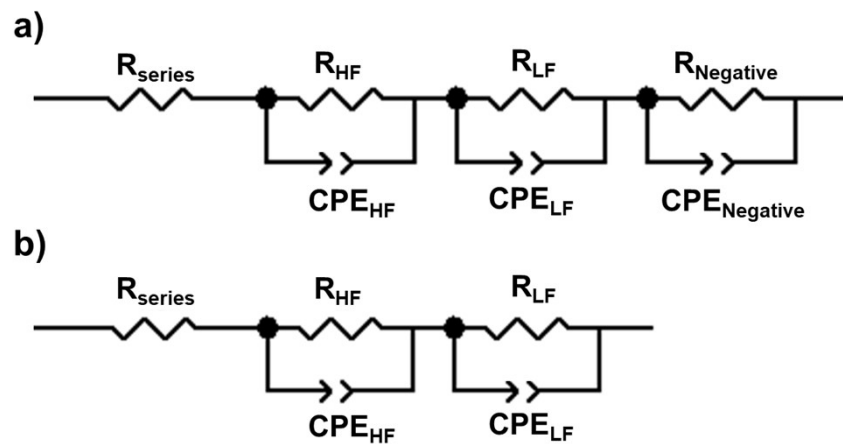
**Figure S2.** 81 individual Sb<sub>2</sub>Se<sub>3</sub> PV devices on a 5x5 cm<sup>2</sup> FTO glass.



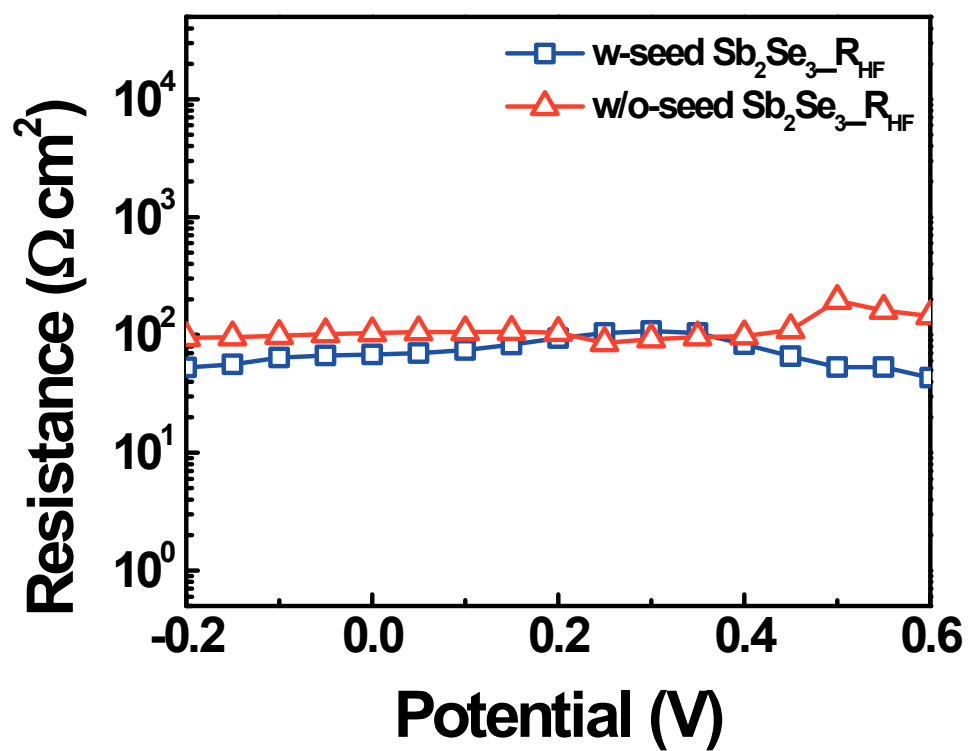
**Figure S3.** Device performance statistics of the a) PCE, b)  $V_{OC}$ , c)  $J_{SC}$ , and d) FF with 81 cells of w-seed  $\text{Sb}_2\text{Se}_3$  PVs. The horizontal middle lines represent the median, the box edges represent the standard deviations.



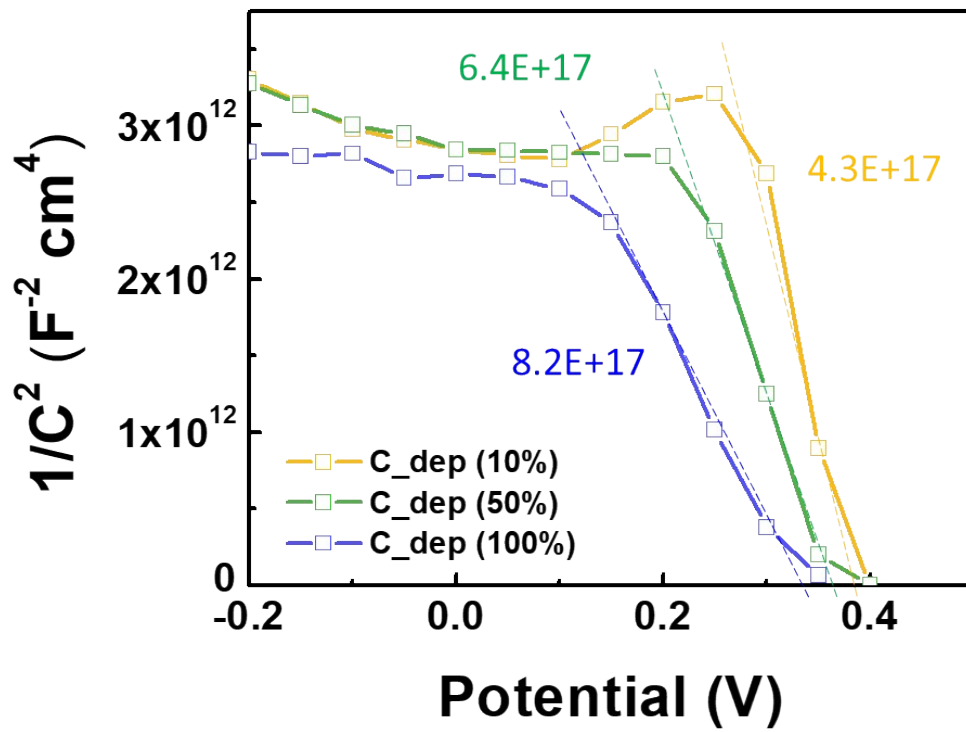
**Figure S4.** Nyquist plots of the w-seed  $\text{Sb}_2\text{Se}_3$  PV at 0 V under 50 and 100% light intensities.



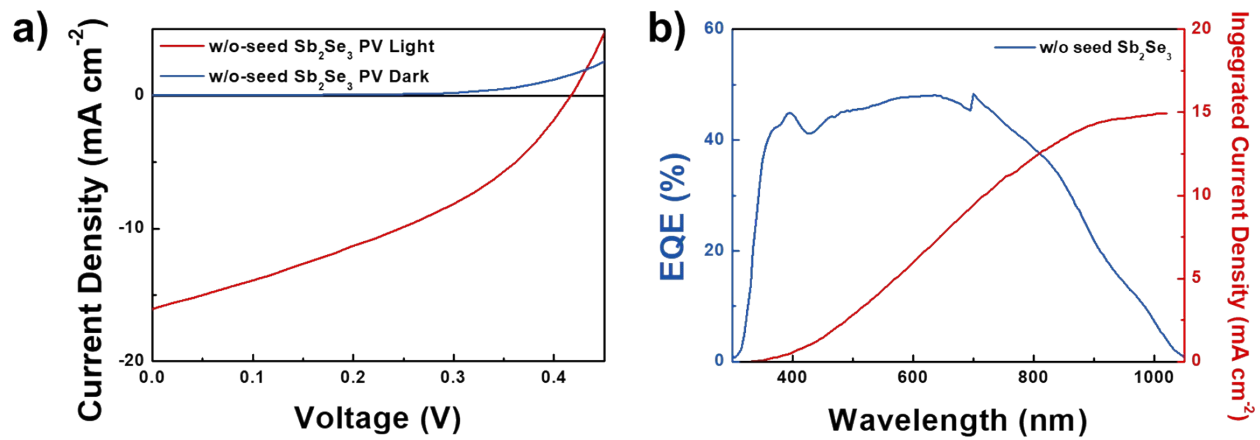
**Figure S5.** Voigt circuit used to fit IS data of a) Figure 2b and b) Figure 2c,d.



**Figure S6.** Resistances from the high frequency semi-circle fitted with the Voight circuit in Figure S5.

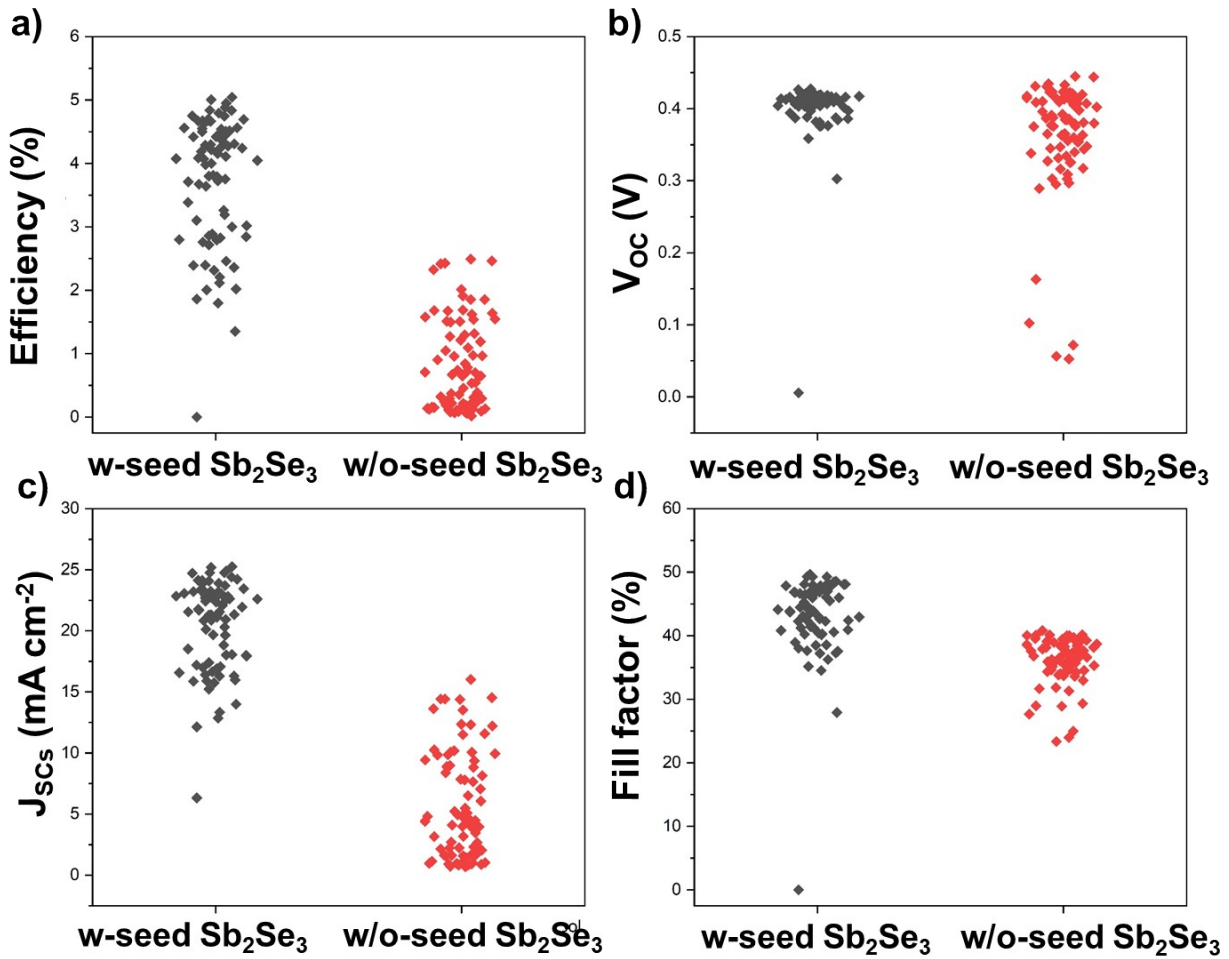


**Figure S7.** Mott-Schottky plots obtained by C\_dep w-seed  $Sb_2Se_3$  PVs under the 10, 50, and 100% light illumination.

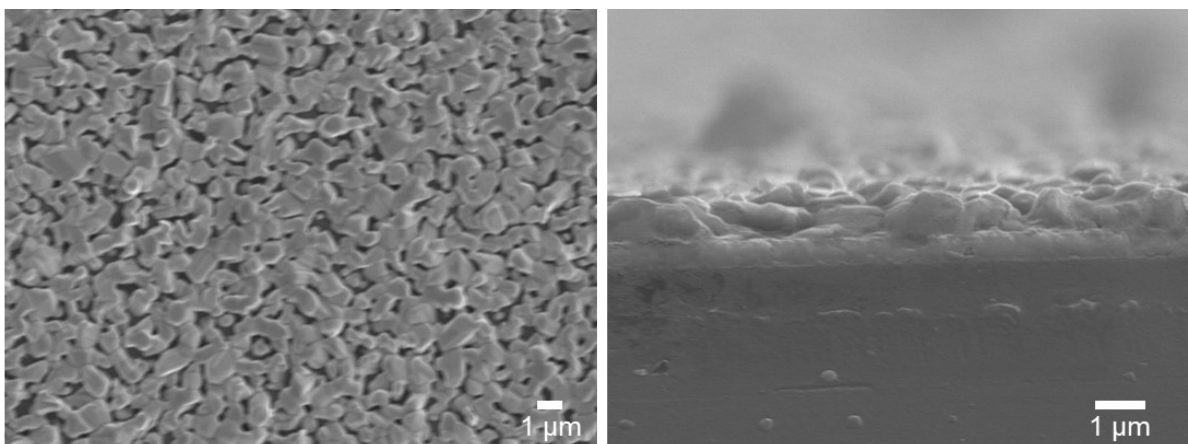


**Figure S8.** a) J–V characteristics of champion w/o-seed  $\text{Sb}_2\text{Se}_3$  PV. b) EQE spectra of a w/o-seed  $\text{Sb}_2\text{Se}_3$  based PV.





**Figure S9.** Device performance statistics comparison between w-seed  $\text{Sb}_2\text{Se}_3$  and w/o-seed  $\text{Sb}_2\text{Se}_3$  of the a) PCE, b)  $V_{\text{OC}}$ , c)  $J_{\text{SC}}$ , and d) FF with 81 cells.



**Figure S10.** a) Top and b) cross-section SEM images of the w/o-seed Sb<sub>2</sub>Se<sub>3</sub> film on TiO<sub>2</sub>/FTO superstrate.

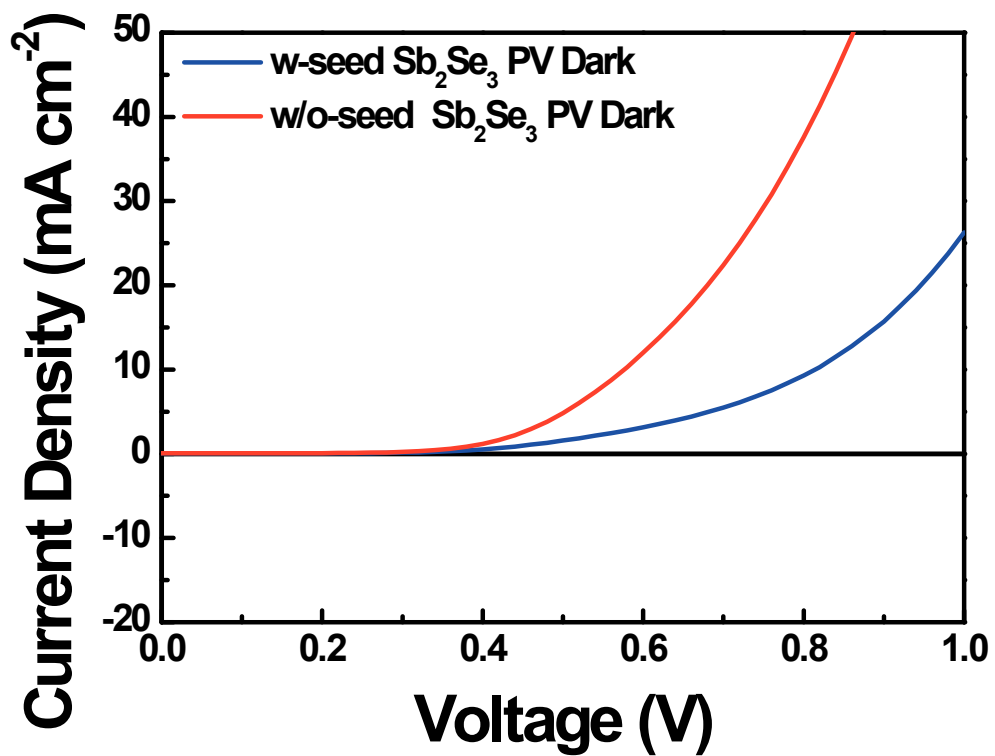


Figure S11. J-V curves of both Sb<sub>2</sub>Se<sub>3</sub> PVs under dark conditions.

### Supplementary Note 1.

Doping density can be calculated from the equation S1, where  $\epsilon$  is the dielectric constant of the semiconductor,  $\epsilon_0$  is the permittivity of free space, A is the area, e is the elementary charge,  $N_d$  is the density of dopants, V is the applied potential,  $V_{fb}$  is the flat band potential,  $k_B$  is the Boltzmann constant, and T is the absolute temperature. Here, one-side junction is assumed due to the higher doping concentration of  $TiO_2$ .

$$\frac{1}{C^2} = \frac{2}{\epsilon\epsilon_0 A e N_d} \left( V - V_{fb} - \frac{k_B T}{e} \right). \quad S1)$$